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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	EBI/EMI, I ² C, IrDA, SmartCard, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	93
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	120-VFBGA
Supplier Device Package	120-BGA (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32gg395f1024-bga120

3.4 Current Consumption

Table 3.3. Current Consumption

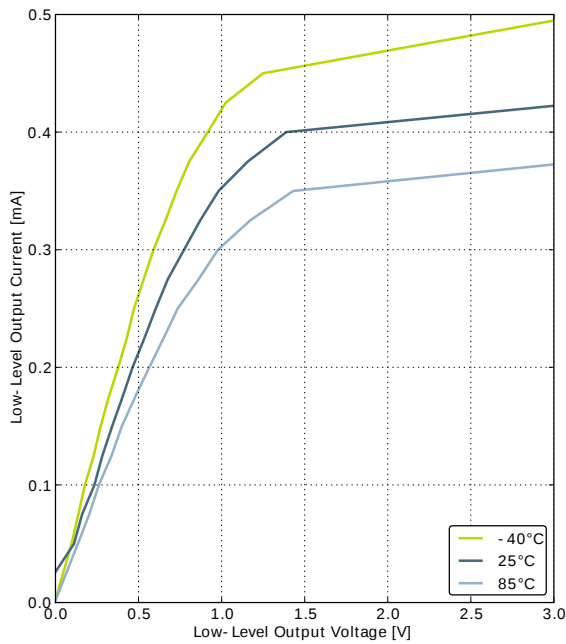
Symbol	Parameter	Condition	Min	Typ	Max	Unit
I _{EM0}	EM0 current. No prescaling. Running prime number calculation code from flash. (Production test condition = 14MHz)	48 MHz HFXO, all peripheral clocks disabled, V _{DD} = 3.0 V		219	240	μA/ MHz
		28 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V		205	225	μA/ MHz
		21 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V		206	229	μA/ MHz
		14 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V		209	232	μA/ MHz
		11 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V		211	234	μA/ MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V		215	242	μA/ MHz
		1.2 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V		243	327	μA/ MHz
I _{EM1}	EM1 current (Production test condition = 14MHz)	48 MHz HFXO, all peripheral clocks disabled, V _{DD} = 3.0 V		80	90	μA/ MHz
		28 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V		80	90	μA/ MHz
		21 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V		81	91	μA/ MHz
		14 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V		83	99	μA/ MHz
		11 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V		85	100	μA/ MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V		90	102	μA/ MHz
		1.2 MHz HFRCO, all peripheral clocks disabled, V _{DD} = 3.0 V		122	152	μA/ MHz
I _{EM2}	EM2 current	EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V _{DD} = 3.0 V, T _{AMB} =25°C		1.1 ¹	1.9 ¹	μA
		EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V _{DD} = 3.0 V, T _{AMB} =85°C		8.8 ¹	21.5 ¹	μA
I _{EM3}	EM3 current	V _{DD} = 3.0 V, T _{AMB} =25°C		0.8 ¹	1.5 ¹	μA
		V _{DD} = 3.0 V, T _{AMB} =85°C		8.2 ¹	20.3 ¹	μA
I _{EM4}	EM4 current	V _{DD} = 3.0 V, T _{AMB} =25°C		0.02	0.08	μA
		V _{DD} = 3.0 V, T _{AMB} =85°C		0.5	2.5	μA

¹ Only one RAM block enabled. The RAM block size is 32 kB.

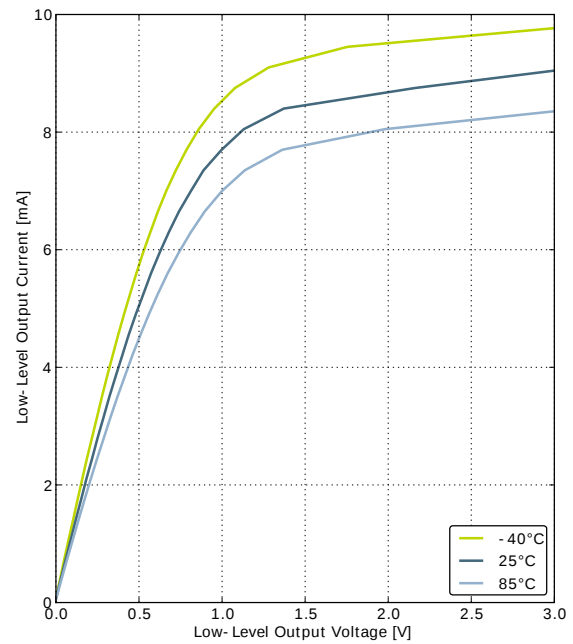
Table 3.5. Power Management

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{BODextthr-}	BOD threshold on falling external supply voltage	EM0	1.74		1.96	V
		EM2	1.74		1.98	V
V _{BODintthr-}	BOD threshold on falling internally regulated supply voltage		1.57		1.70	V
V _{BODextthr+}	BOD threshold on rising external supply voltage			1.85	1.98	V
V _{PORthr+}	Power-on Reset (POR) threshold on rising external supply voltage				1.98	V
t _{RESET}	Delay from reset is released until program execution starts	Applies to Power-on Reset, Brown-out Reset and pin reset.		163		μs
C _{DECOUPLE}	Voltage regulator decoupling capacitor.	X5R capacitor recommended. Apply between DECOUPLE pin and GROUND		1		μF
C _{USB_VREGO}	USB voltage regulator out decoupling capacitor.	X5R capacitor recommended. Apply between USB_VREGO pin and GROUND		1		μF
C _{USB_VREGI}	USB voltage regulator in decoupling capacitor.	X5R capacitor recommended. Apply between USB_VREGI pin and GROUND		4.7		μF

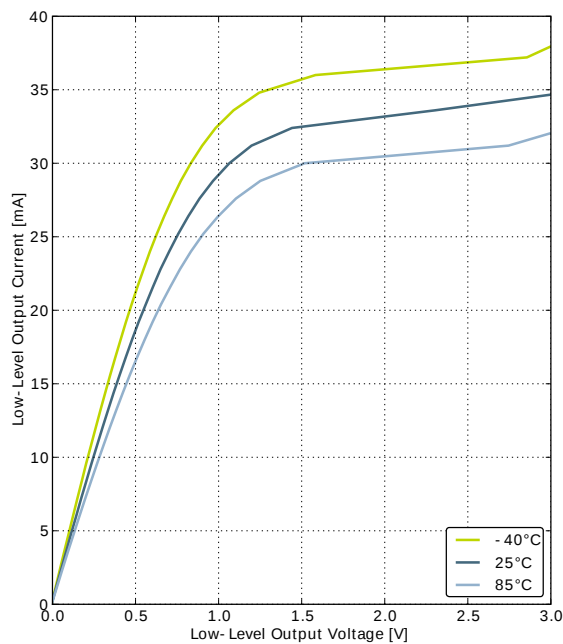
Figure 3.6. Typical Low-Level Output Current, 3V Supply Voltage



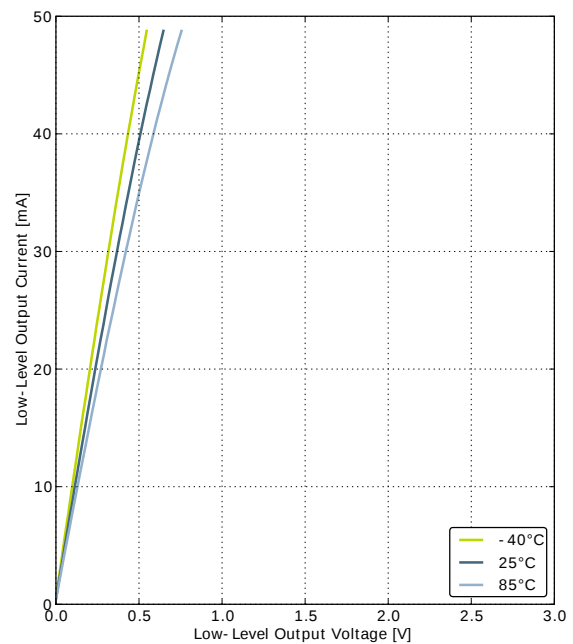
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD



GPIO_Px_CTRL DRIVEMODE = HIGH

3.9 Oscillators

3.9.1 LFXO

Table 3.8. LFXO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFXO}	Supported nominal crystal frequency			32.768		kHz
ESR_{LFXO}	Supported crystal equivalent series resistance (ESR)			30	120	kOhm
C_{LFXOL}	Supported crystal external load range		$\times^1$		25	pF
DC_{LFXO}	Duty cycle		48	50	53.5	%
I_{LFXO}	Current consumption for core and buffer after startup.	ESR=30 kOhm, C_L =10 pF, LFXOBOOST in CMU_CTRL is 1		190		nA
t_{LFXO}	Start- up time.	ESR=30 kOhm, C_L =10 pF, 40% - 60% duty cycle has been reached, LFXOBOOST in CMU_CTRL is 1		400		ms

¹See Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup in energyAware Designer in Simplicity Studio

For safe startup of a given crystal, the Configurator tool in Simplicity Studio contains a tool to help users configure both load capacitance and software settings for using the LFXO. For details regarding the crystal configuration, the reader is referred to application note "AN0016 EFM32 Oscillator Design Consideration".

3.9.2 HFXO

Table 3.9. HFXO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{HFXO}	Supported nominal crystal Frequency		4		48	MHz
ESR_{HFXO}	Supported crystal equivalent series resistance (ESR)	Crystal frequency 48 MHz			50	Ohm
		Crystal frequency 32 MHz		30	60	Ohm
		Crystal frequency 4 MHz		400	1500	Ohm
g_{mHFXO}	The transconductance of the HFXO input transistor at crystal startup	HFXOBOOST in CMU_CTRL equals 0b11	20			mS
C_{HFXOL}	Supported crystal external load range		5		25	pF
I_{HFXO}	Current consumption for HFXO after startup	4 MHz: ESR=400 Ohm, C_L =20 pF, HFXOBOOST in CMU_CTRL equals 0b11		85		μ A
		32 MHz: ESR=30 Ohm, C_L =10 pF, HFXOBOOST in CMU_CTRL equals 0b11		165		μ A
t_{HFXO}	Startup time	32 MHz: ESR=30 Ohm, C_L =10 pF, HFXOBOOST in CMU_CTRL equals 0b11		400		μ s

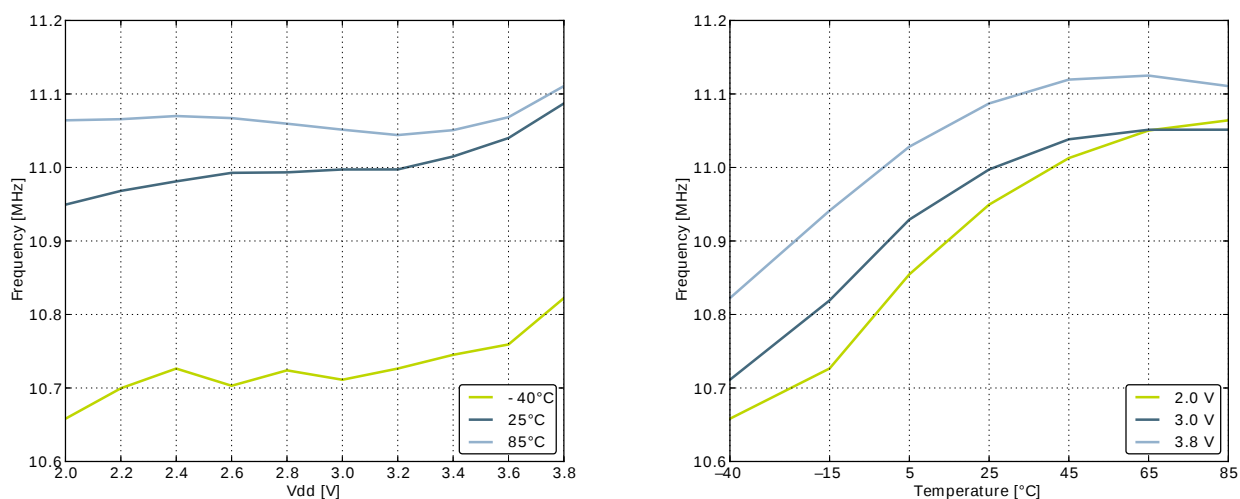
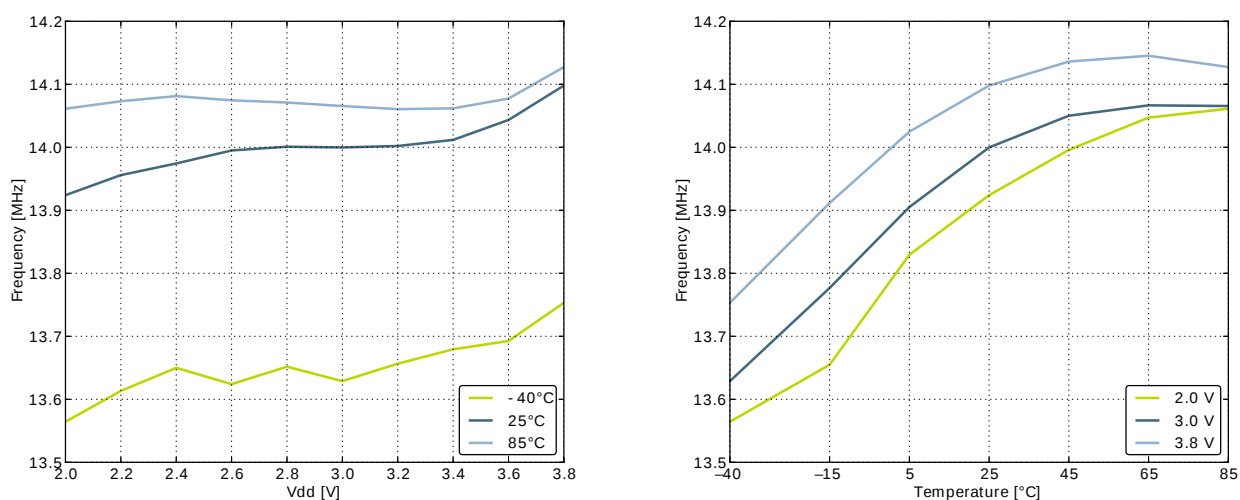
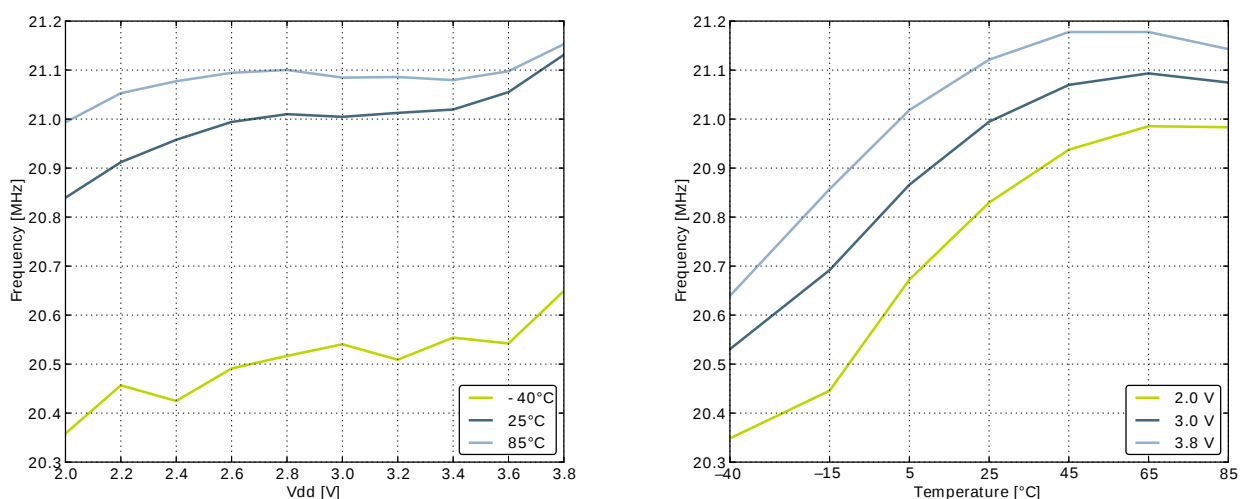
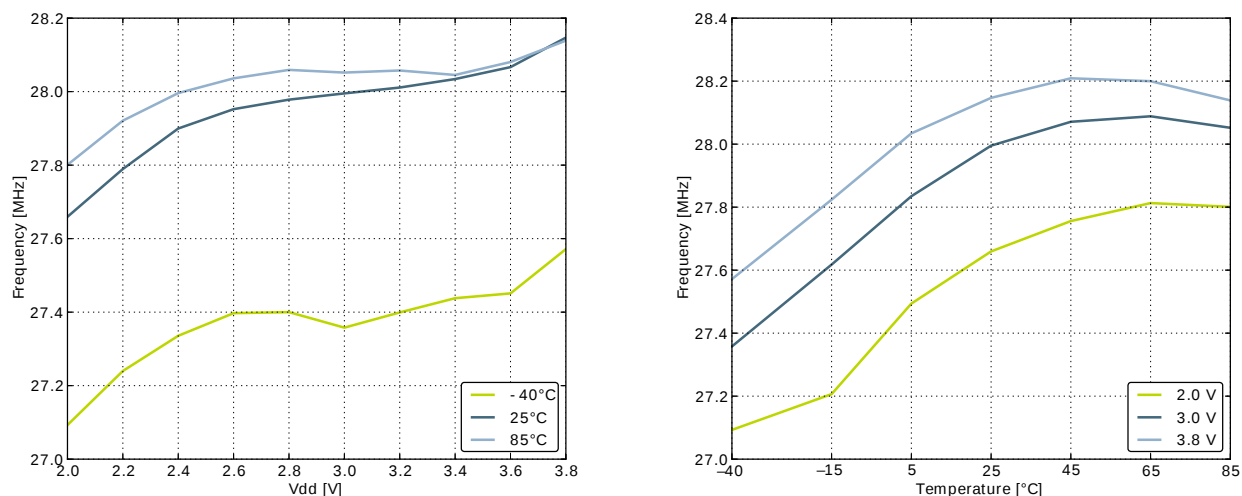
Figure 3.13. Calibrated HFRCO 11 MHz Band Frequency vs Supply Voltage and Temperature**Figure 3.14. Calibrated HFRCO 14 MHz Band Frequency vs Supply Voltage and Temperature****Figure 3.15. Calibrated HFRCO 21 MHz Band Frequency vs Supply Voltage and Temperature**

Figure 3.16. Calibrated HFRCO 28 MHz Band Frequency vs Supply Voltage and Temperature

3.9.5 AUXHFRCO

Table 3.12. AUXHFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{AUXHFRCO}	Oscillation frequency, $V_{\text{DD}} = 3.0 \text{ V}$, $T_{\text{AMB}} = 25^\circ\text{C}$	28 MHz frequency band	27.5	28.0	28.5	MHz
		21 MHz frequency band	20.6	21.0	21.4	MHz
		14 MHz frequency band	13.7	14.0	14.3	MHz
		11 MHz frequency band	10.8	11.0	11.2	MHz
		7 MHz frequency band	6.48 ¹	6.60 ¹	6.72 ¹	MHz
		1 MHz frequency band	1.15 ²	1.20 ²	1.25 ²	MHz
$t_{\text{AUXHFRCO_settling}}$	Settling time after start-up	$f_{\text{AUXHFRCO}} = 14 \text{ MHz}$		0.6		Cycles
$\text{DC}_{\text{AUXHFRCO}}$	Duty cycle	$f_{\text{AUXHFRCO}} = 14 \text{ MHz}$	48.5	50	51	%
$\text{TUNESTEP}_{\text{AUXHFRCO}}$	Frequency step for LSB change in TUNING value			0.3 ³		%

¹For devices with prod. rev. < 19, Typ = 7MHz and Min/Max values not applicable.

²For devices with prod. rev. < 19, Typ = 1MHz and Min/Max values not applicable.

³The TUNING field in the CMU_AUXHFRCOCTRL register may be used to adjust the AUXHFRCO frequency. There is enough adjustment range to ensure that the frequency bands above 7 MHz will always have some overlap across supply voltage and temperature. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the AUXHFRCO frequency at any arbitrary value between 7 MHz and 28 MHz across operating conditions.

3.9.6 ULFRCO

Table 3.13. ULFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{ULFRCO}	Oscillation frequency	25°C, 3V	0.70		1.75	kHz
TC_{ULFRCO}	Temperature coefficient			0.05		%/°C
VC_{ULFRCO}	Supply voltage coefficient			-18.2		%/V

3.10 Analog Digital Converter (ADC)

Table 3.14. ADC

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{ADCIN}	Input voltage range	Single ended	0		V_{REF}	V
		Differential	$-V_{REF}/2$		$V_{REF}/2$	V
$V_{ADCREFIN}$	Input range of external reference voltage, single ended and differential		1.25		V_{DD}	V
$V_{ADCREFIN_CH7}$	Input range of external negative reference voltage on channel 7	See $V_{ADCREFIN}$	0		$V_{DD} - 1.1$	V
$V_{ADCREFIN_CH6}$	Input range of external positive reference voltage on channel 6	See $V_{ADCREFIN}$	0.625		V_{DD}	V
$V_{ADCCMIN}$	Common mode input range		0		V_{DD}	V
I_{ADCIN}	Input current	2pF sampling capacitors		<100		nA
$CMRR_{ADC}$	Analog input common mode rejection ratio			65		dB
I_{ADC}	Average active current	1 MSamples/s, 12 bit, external reference		351		μA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b00		67		μA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b01		63		μA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUP-MODE in ADCn_CTRL set to 0b10		64		μA
I_{ADCREF}	Current consumption of internal voltage reference	Internal voltage reference		65		μA

Symbol	Parameter	Condition	Min	Typ	Max	Unit
GAIN _{ED}	Gain error drift	1.25V reference		0.01 ²	0.033 ³	%/°C
		2.5V reference		0.01 ²	0.03 ³	%/°C
OFFSET _{ED}	Offset error drift	1.25V reference		0.2 ²	0.7 ³	LSB/°C
		2.5V reference		0.2 ²	0.62 ³	LSB/°C

¹On the average every ADC will have one missing code, most likely to appear around 2048 +/- n*512 where n can be a value in the set {-3, -2, -1, 1, 2, 3}. There will be no missing code around 2048, and in spite of the missing code the ADC will be monotonic at all times so that a response to a slowly increasing input will always be a slowly increasing output. Around the one code that is missing, the neighbour codes will look wider in the DNL plot. The spectra will show spurs on the level of -78dBc for a full scale input for chips that have the missing code issue.

²Typical numbers given by $\text{abs}(\text{Mean}) / (85 - 25)$.

³Max number given by $(\text{abs}(\text{Mean}) + 3 \times \text{stddev}) / (85 - 25)$.

The integral non-linearity (INL) and differential non-linearity parameters are explained in Figure 3.17 (p. 32) and Figure 3.18 (p. 33), respectively.

Figure 3.17. Integral Non-Linearity (INL)

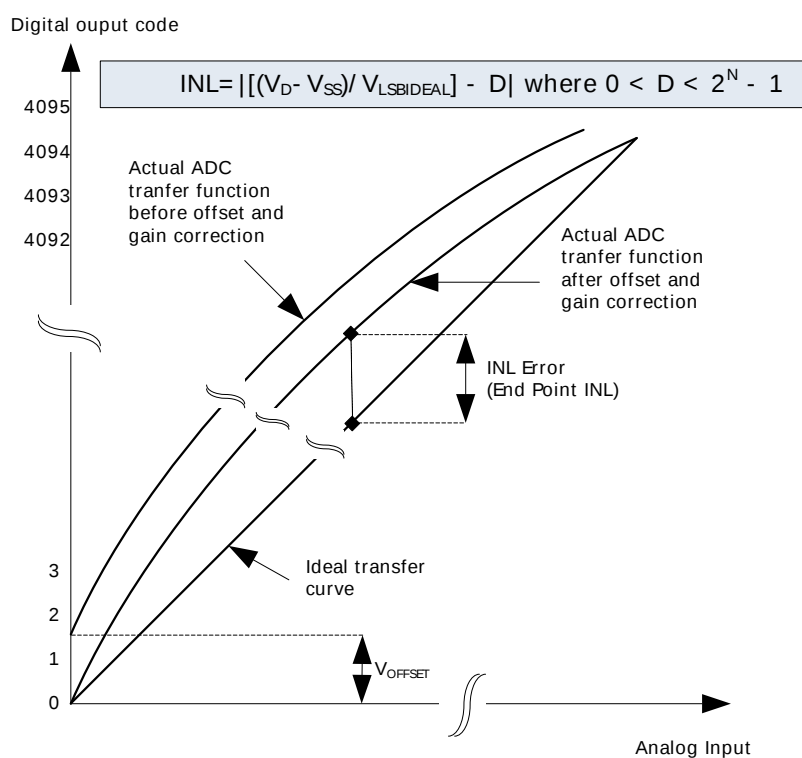
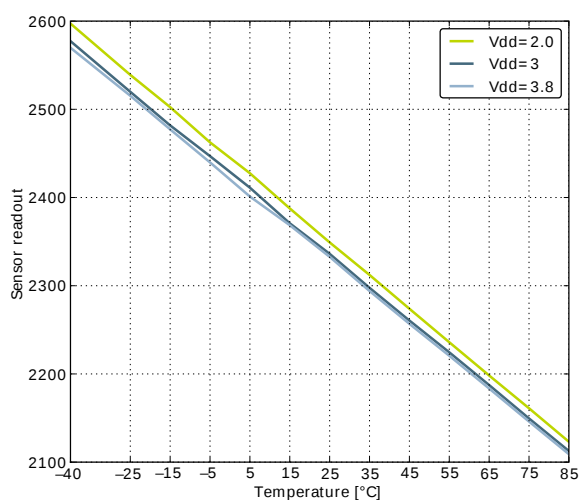


Figure 3.24. ADC Temperature sensor readout

3.11 Digital Analog Converter (DAC)

Table 3.15. DAC

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{DACOUT}	Output voltage range	VDD voltage reference, single ended	0		V_{DD}	V
		VDD voltage reference, differential	$-V_{DD}$		V_{DD}	V
V_{DACCM}	Output common mode voltage range		0		V_{DD}	V
I_{DAC}	Active current including references for 2 channels	500 kSamples/s, 12 bit		400 ¹	600 ¹	μA
		100 kSamples/s, 12 bit		200 ¹	260 ¹	μA
		1 kSamples/s 12 bit NORMAL		17 ¹	25 ¹	μA
SR_{DAC}	Sample rate				500	ksamples/s
f_{DAC}	DAC clock frequency	Continuous Mode			1000	kHz
		Sample/Hold Mode			250	kHz
		Sample/Off Mode			250	kHz
$CYC_{DACCONV}$	Clock cycles per conversion			2		
$t_{DACCONV}$	Conversion time		2			μs
$t_{DACSETTLE}$	Settling time			5		μs
SNR_{DAC}	Signal to Noise Ratio (SNR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		58		dB
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		59		dB
		500 kSamples/s, 12 bit, differential, internal 1.25V reference		58		dB

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		500 kSamples/s, 12 bit, differential, internal 2.5V reference		58		dB
		500 kSamples/s, 12 bit, differential, V_{DD} reference		59		dB
SNDR _{DAC}	Signal to Noise-pulse Distortion Ratio (SNDR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		57		dB
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		54		dB
		500 kSamples/s, 12 bit, differential, internal 1.25V reference		56		dB
		500 kSamples/s, 12 bit, differential, internal 2.5V reference		53		dB
		500 kSamples/s, 12 bit, differential, V_{DD} reference		55		dB
SFDR _{DAC}	Spurious-Free Dynamic Range(SFDR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		62		dBc
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		56		dBc
		500 kSamples/s, 12 bit, differential, internal 1.25V reference		61		dBc
		500 kSamples/s, 12 bit, differential, internal 2.5V reference		55		dBc
		500 kSamples/s, 12 bit, differential, V_{DD} reference		60		dBc
V _{DACOFFSET}	Offset voltage	After calibration, single ended		2	12	mV
		After calibration, differential		2		mV
DNL _{DAC}	Differential non-linearity			±1		LSB
INL _{DAC}	Integral non-linearity			±5		LSB
MC _{DAC}	No missing codes			12		bits

¹ Measured with a static input code and no loading on the output.

3.12 Operational Amplifier (OPAMP)

The electrical characteristics for the Operational Amplifiers are based on simulations.

Table 3.16. OPAMP

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I _{OPAMP}	Active Current	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0, Unity Gain		350	405	μA
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1, Unity Gain		95	115	μA

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1, Unity Gain		13	17	μA
G _{OL}	Open Loop Gain	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		101		dB
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		98		dB
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		91		dB
GBW _{OPAMP}	Gain Bandwidth Product	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		6.1		MHz
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		1.8		MHz
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		0.25		MHz
PM _{OPAMP}	Phase Margin	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0, C _L =75 pF		64		°
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1, C _L =75 pF		58		°
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1, C _L =75 pF		58		°
R _{INPUT}	Input Resistance			100		Mohm
R _{LOAD}	Load Resistance		200			Ohm
I _{LOAD_DC}	DC Load Current				11	mA
V _{INPUT}	Input Voltage	OPAxHCMDIS=0	V _{SS}		V _{DD}	V
		OPAxHCMDIS=1	V _{SS}		V _{DD} -1.2	V
V _{OUTPUT}	Output Voltage		V _{SS}		V _{DD}	V
V _{OFFSET}	Input Offset Voltage	Unity Gain, V _{SS} <V _{in} <V _{DD} , OPAxHCMDIS=0	-13	0	11	mV
		Unity Gain, V _{SS} <V _{in} <V _{DD} -1.2, OPAxHCMDIS=1		1		mV
V _{OFFSET_DRIFT}	Input Offset Voltage Drift				0.02	mV/°C
SR _{OPAMP}	Slew Rate	(OPA2)BIASPROG=0xF, (OPA2)HALFBIAS=0x0		3.2		V/μs
		(OPA2)BIASPROG=0x7, (OPA2)HALFBIAS=0x1		0.8		V/μs
		(OPA2)BIASPROG=0x0, (OPA2)HALFBIAS=0x1		0.1		V/μs
N _{OPAMP}	Voltage Noise	V _{out} =1V, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx- HCMDIS=0		101		μV _{RMS}
		V _{out} =1V, RESSEL=0, 0.1 Hz<f<10 kHz, OPAx- HCMDIS=1		141		μV _{RMS}

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		$V_{out}=1V$, RESSEL=0, 0.1 Hz< f <1 MHz, OPAXHCMDIS=0		196		μV_{RMS}
		$V_{out}=1V$, RESSEL=0, 0.1 Hz< f <1 MHz, OPAXHCMDIS=1		229		μV_{RMS}
		RESSEL=7, 0.1 Hz< f <10 kHz, OPAXHCMDIS=0		1230		μV_{RMS}
		RESSEL=7, 0.1 Hz< f <10 kHz, OPAXHCMDIS=1		2130		μV_{RMS}
		RESSEL=7, 0.1 Hz< f <1 MHz, OPAXHCMDIS=0		1630		μV_{RMS}
		RESSEL=7, 0.1 Hz< f <1 MHz, OPAXHCMDIS=1		2590		μV_{RMS}

Figure 3.25. OPAMP Common Mode Rejection Ratio

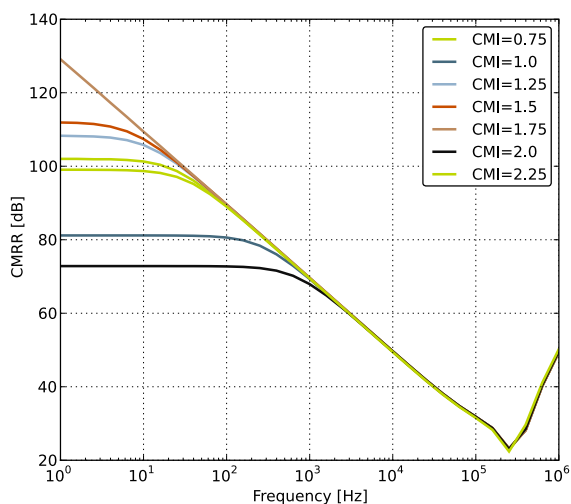


Figure 3.26. OPAMP Positive Power Supply Rejection Ratio

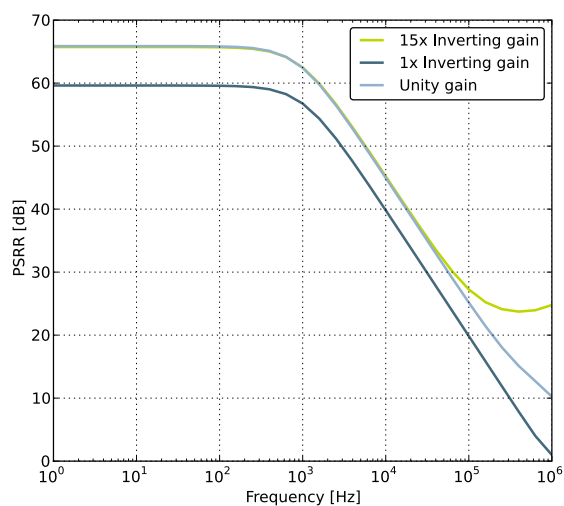
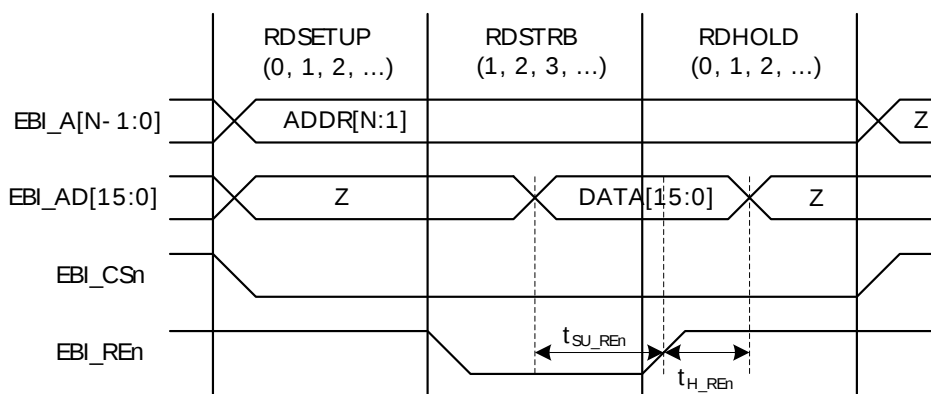


Figure 3.34. EBI Read Enable Related Timing Requirements**Table 3.22. EBI Read Enable Related Timing Requirements**

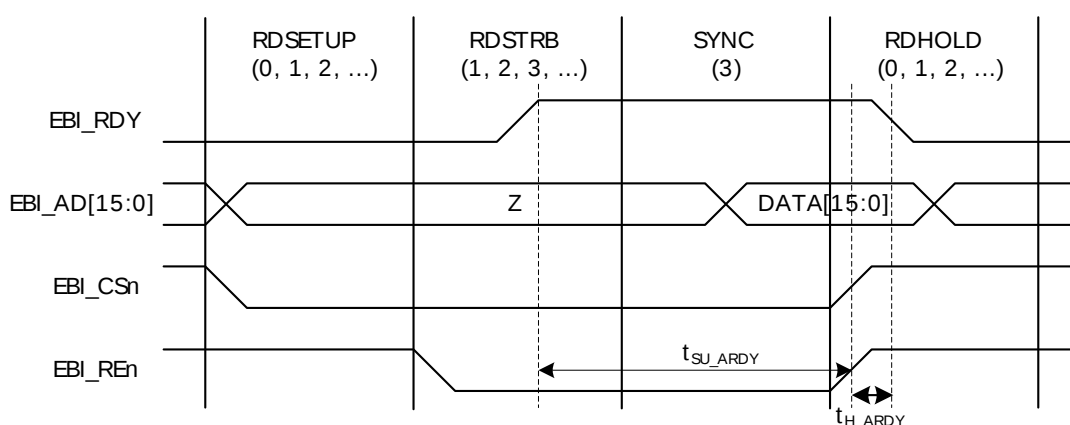
Symbol	Parameter	Min	Typ	Max	Unit
$t_{SU_REn}^{1\ 2\ 3\ 4}$	Setup time, from EBI_AD valid to trailing EBI_REn edge		37		ns
$t_{H_Ren}^{1\ 2\ 3\ 4}$	Hold time, from trailing EBI_REn edge to EBI_AD invalid		-1		ns

¹Applies for all addressing modes (figure only shows D16A8).

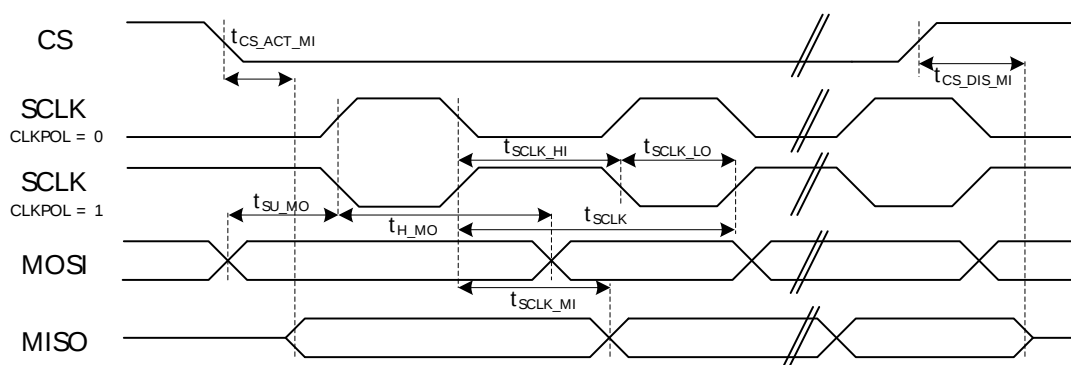
²Applies for both EBI_REn and EBI_NANDREn (figure only shows EBI_REn)

³Applies for all polarities (figure only shows active low signals)

⁴Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

Figure 3.35. EBI Ready/Wait Related Timing Requirements**Table 3.23. EBI Ready/Wait Related Timing Requirements**

Symbol	Parameter	Min	Typ	Max	Unit
$t_{SU_ARDY}^{1\ 2\ 3\ 4}$	Setup time, from EBI_ARDY valid to trailing EBI_REn, EBI_WEn edge	$37 + (3 * t_{HFCORECLK})$			ns

Figure 3.37. SPI Slave Timing**Table 3.28. SPI Slave Timing**

Symbol	Parameter	Min	Typ	Max	Unit
$t_{SCLK_sl}^{1,2}$	SCKL period	$2 * t_{HFPER-CLK}$			ns
$t_{SCLK_hi}^{1,2}$	SCLK high period	$3 * t_{HFPER-CLK}$			ns
$t_{SCLK_lo}^{1,2}$	SCLK low period	$3 * t_{HFPER-CLK}$			ns
$t_{CS_ACT_MI}^{1,2}$	CS active to MISO	4.00		30.00	ns
$t_{CS_DIS_MI}^{1,2}$	CS disable to MISO	4.00		30.00	ns
$t_{SU_MO}^{1,2}$	MOSI setup time	4.00			ns
$t_{H_MO}^{1,2}$	MOSI hold time	$2 + 2 * t_{HF-CLK}$			ns
$t_{SCLK_MI}^{1,2}$	SCLK to MISO	$9 + t_{HFPER-CLK}$		$36 + 2 * t_{HF-CLK}$	ns

¹Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)

²Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

3.18 USB

The USB hardware in the EFM32GG395 passes all tests for USB 2.0 Full Speed certification. See the test-report distributed with application note "AN0046 - USB Hardware Design Guide".

3.19 Digital Peripherals

Table 3.29. Digital Peripherals

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{USART}	USART current	USART idle current, clock enabled		4.9		$\mu A / MHz$
I_{UART}	UART current	UART idle current, clock enabled		3.4		$\mu A / MHz$
I_{LEUART}	LEUART current	LEUART idle current, clock enabled		140		nA
I_{I2C}	I2C current	I2C idle current, clock enabled		6.1		$\mu A / MHz$

4 Pinout and Package

Note

Please refer to the application note "AN0002 EFM32 Hardware Design Considerations" for guidelines on designing Printed Circuit Boards (PCB's) for the EFM32GG395.

4.1 Pinout

The EFM32GG395 pinout is shown in Figure 4.1 (p. 53) and Table 4.1 (p. 53). Alternate locations are denoted by "#" followed by the location number (Multiple locations on the same pin are split with "/"). Alternate locations can be configured in the LOCATION bitfield in the *_ROUTE register in the module in question.

Figure 4.1. EFM32GG395 Pinout (top view, not to scale)

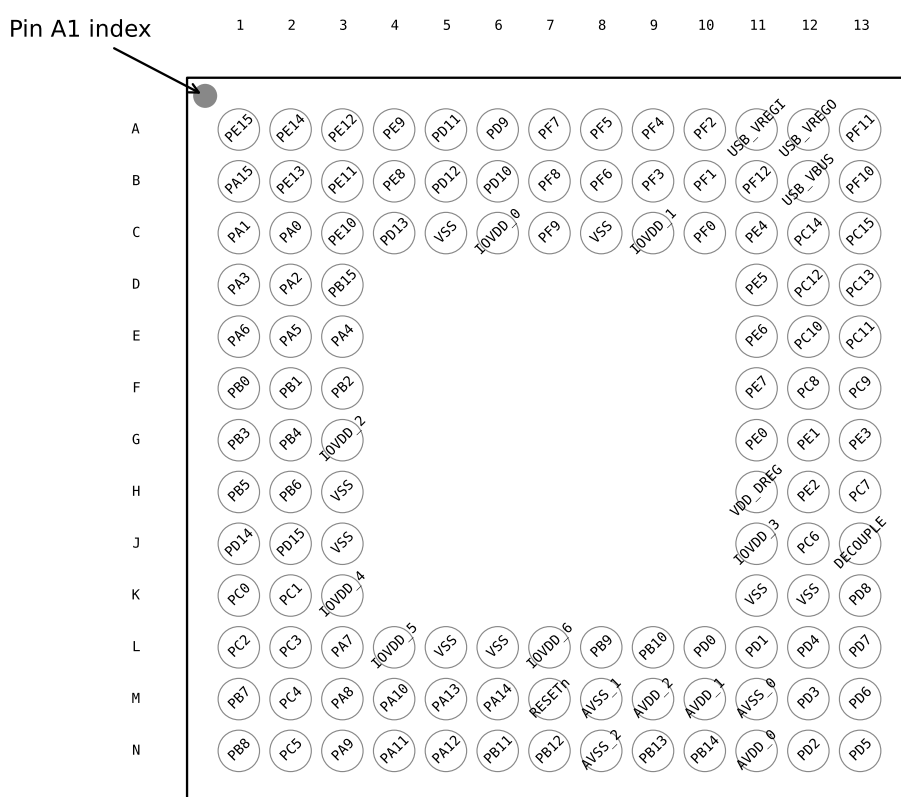
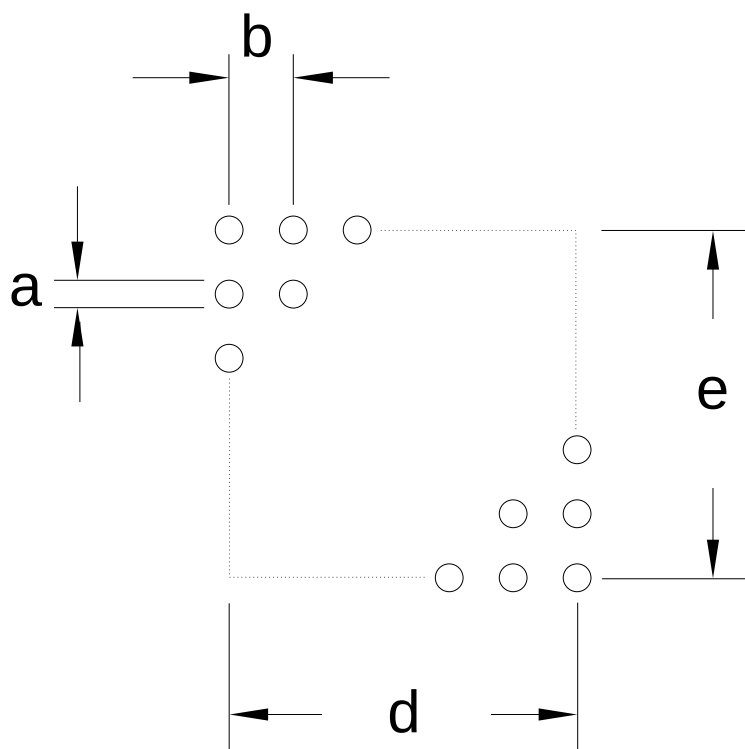


Table 4.1. Device Pinout

BGA120 Pin# and Name		Pin Alternate Functionality / Description				
Pin #	Pin Name	Analog	EBI	Timers	Communication	Other
A1	PE15		EBI_AD07 #0/1/2	TIM3_CC1 #0	LEU0_RX #2	
A2	PE14		EBI_AD06 #0/1/2	TIM3_CC0 #0	LEU0_TX #2	
A3	PE12		EBI_AD04 #0/1/2	TIM1_CC2 #1	US0_RX #3 US0_CLK #0 I2C0_SDA #6	CMU_CLK1 #2 LES_ALTEX6 #0

BGA120 Pin# and Name		Pin Alternate Functionality / Description				
Pin #	Pin Name	Analog	EBI	Timers	Communication	Other
H11	VDD_DREG	Power supply for on-chip voltage regulator.				
H12	PE2	BU_VOUT	EBI_A09 #0	TIM3_CC2 #1	U1_TX #3	ACMP0_O #1
H13	PC7	ACMP0_CH7	EBI_A06 #0/1/2		I2C0_SCL #2 LEU1_RX #0	LES_CH7 #0 ETM_TD0 #2
J1	PD14				I2C0_SDA #3	
J2	PD15				I2C0_SCL #3	
J3	VSS	Ground.				
J11	IOVDD_3	Digital IO power supply 3.				
J12	PC6	ACMP0_CH6	EBI_A05 #0/1/2		I2C0_SDA #2 LEU1_TX #0	LES_CH6 #0 ETM_TCLK #2
J13	DECOUPLE	Decouple output for on-chip voltage regulator. An external capacitance of size C _{DECOUPLE} is required at this pin.				
K1	PC0	ACMP0_CH0 DAC0_OUT0ALT #0/ OPAMP_OUT0ALT	EBI_A23 #0/1/2	TIM0_CC1 #4 PCNT0_S0IN #2	US0_TX #5 US1_TX #0 I2C0_SDA #4	LES_CH0 #0 PRS_CH2 #0
K2	PC1	ACMP0_CH1 DAC0_OUT0ALT #1/ OPAMP_OUT0ALT	EBI_A24 #0/1/2	TIM0_CC2 #4 PCNT0_S1IN #2	US0_RX #5 US1_RX #0 I2C0_SCL #4	LES_CH1 #0 PRS_CH3 #0
K3	IOVDD_4	Digital IO power supply 4.				
K11	VSS	Ground.				
K12	VSS	Ground.				
K13	PD8	BU_VIN				CMU_CLK1 #1
L1	PC2	ACMP0_CH2 DAC0_OUT0ALT #2/ OPAMP_OUT0ALT	EBI_A25 #0/1/2	TIM0_CDTI0 #4	US2_TX #0	LES_CH2 #0
L2	PC3	ACMP0_CH3 DAC0_OUT0ALT #3/ OPAMP_OUT0ALT	EBI_NANDREn #0/1/2	TIM0_CDTI1 #4	US2_RX #0	LES_CH3 #0
L3	PA7		EBI_CSTFT #0/1/2			
L4	IOVDD_5	Digital IO power supply 5.				
L5	VSS	Ground.				
L6	VSS	Ground.				
L7	IOVDD_6	Digital IO power supply 6.				
L8	PB9		EBI_A03 #0/1/2		U1_TX #2	
L9	PB10		EBI_A04 #0/1/2		U1_RX #2	
L10	PD0	ADC0_CH0 DAC0_OUT0ALT #4/ OPAMP_OUT0ALT OPAMP_OUT2 #1		PCNT2_S0IN #0	US1_TX #1	
L11	PD1	ADC0_CH1 DAC0_OUT1ALT #4/ OPAMP_OUT1ALT		TIM0_CC0 #3 PCNT2_S1IN #0	US1_RX #1	DBG_SWO #2
L12	PD4	ADC0_CH4 OPAMP_P2			LEU0_TX #0	ETM_TD2 #0/2
L13	PD7	ADC0_CH7 OPAMP_N1		LETIM0_OUT1 #0 TIM1_CC1 #4 PCNT0_S1IN #3	US1_TX #2 I2C0_SCL #1	CMU_CLK0 #2 LES_ALTEX1 #0 ACMP1_O #2 ETM_TCLK #0
M1	PB7	LFXTAL_P		TIM1_CC0 #3	US0_TX #4 US1_CLK #0	

Figure 5.3. BGA120 PCB Stencil Design**Table 5.3. BGA120 PCB Stencil Design Dimensions (Dimensions in mm)**

Symbol	Dim. (mm)
a	0.25
b	0.50
d	6.00
e	6.00

1. The drawings are not to scale.
2. All dimensions are in millimeters.
3. All drawings are subject to change without notice.
4. The PCB Land Pattern drawing is in compliance with IPC-7351B.
5. Stencil thickness 0.125 mm.
6. For detailed pin-positioning, see Figure 4.3 (p. 65) .

5.2 Soldering Information

The latest IPC/JEDEC J-STD-020 recommendations for Pb-Free reflow soldering should be followed.

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